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TOSHIBA Photocoupler GaAs Ired & Photo-Triac

TLP561G

Triac Driver Programmable Controllers AC-Output Module Solid State Relay

The TOSHIBA TLP561G consists of a zero voltage crossing turn–on photo–triac optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP package.

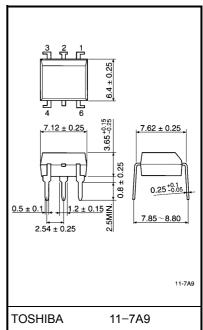
- Peak off-state voltage: 400V(min.)
- On-state current: 100mA(max.)
- Isolation voltage: 2500V_{rms}(min.)
- UL recognized: file no. E67349
- Isolation operating voltage: $2500V_{ac}$ or $300V_{dc}$ for isolation groupe C^{*1}
- Trigger LED current

Classi– fication*	Trigger LED Current (mA) $V_T = 6V$, Ta = 25°C		Marking Of Classification
(IFT5)	Min. —	Max. 5	T5
(IFT7)	_	7	T5, T7
Standard	_	10	T5, T7, blank

*Ex. (IFT5); TLP561G (IFT5)

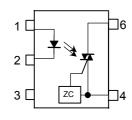
(Note) Application type name for certification test, please use standard product type name, i.e. TLP561G (IFT5): TLP561G

*1: According to VDE0110, table 4.



Weight: 0.39g

Pin Configuration (top view)





2 : CATHODE

3 : N.C.

4 : TERMINAL 1 6 : TERMINAL 2

Maximum Ratings (Ta = 25°C)

Characteristic			Symbol	Rating	Unit	
	Forward current	١ _F	50	mA		
	Forward current derating (Ta ≥ \$	ΔI _F / °C	-0.7	mA / °C		
LED	Peak forward current (100µs pu	I _{FP}	1	Α		
	Reverse voltage	Reverse voltage			V	
	Junction temperature	Tj	125	°C		
	Off-state ontput terminal voltage		V _{DRM}	400	V	
	On-state RMS current	Ta = 25°C		100	mA	
Detector		Ta = 70°C	I _{T(RMS)}	50	IIIA	
	On–state current derating (Ta ≥	ΔI _T / °C	-1.1	mA / °C		
	Peak on-state current (100µs p	I _{TP}	2	A		
	Peak nonrepetitive surge curren (Pw = 10ms, DC = 10%)	ITSM	1.2	А		
	Junction temperature	Tj	115	°C		
Storage temperature range			T _{stg}	-55~125	°C	
Operating temperature range			T _{opr}	-40~100	°C	
Lead soldering temperature (10s)			T _{sol}	260	°C	
Isolation voltage (AC, 1 min., R.H. \leq 60%)		BVS	2500	V _{rms}		

Recommended Operating Conditions

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Supply voltage	V _{AC}			120	V _{ac}
Forward current	١ _F	15	20	25	mA
Peak on-state current	I _{TP}			1	А
Operating temperature	T _{opr}	-25	_	85	°C

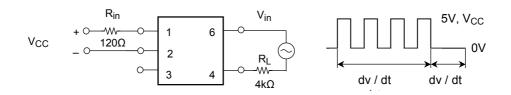
Individual Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min.	Тур.	Max.	Unit
LED	Forward voltage	VF	I _F = 10mA	1.0	1.15	1.3	V
	Reverse current	I _R	V _R = 5V		_	10	μA
	Capacitance	CT	V = 0, f = 1MHz		30	-	pF
Detector	Peak off-state current	I _{DRM}	V _{DRM} = 400V	_	10	100	nA
	Peak on-state voltage	V _{TM}	I _{TM} = 100mA	_	1.7	3.0	V
	Holding current	Ι _Η	—	—	0.6	_	mA
	Critical rate of rise of off–state voltage	dv / dt	V _{in} = 120V _{rms} , Ta = 85°C (Fig	.1) 200	500	_	V / µs
	Critical rate or rise of commutating voltage	dv / dt (c)	V _{in} = 30V _{rms} , I _T = 15mA (Fig	.1) —	0.2	_	V / µs

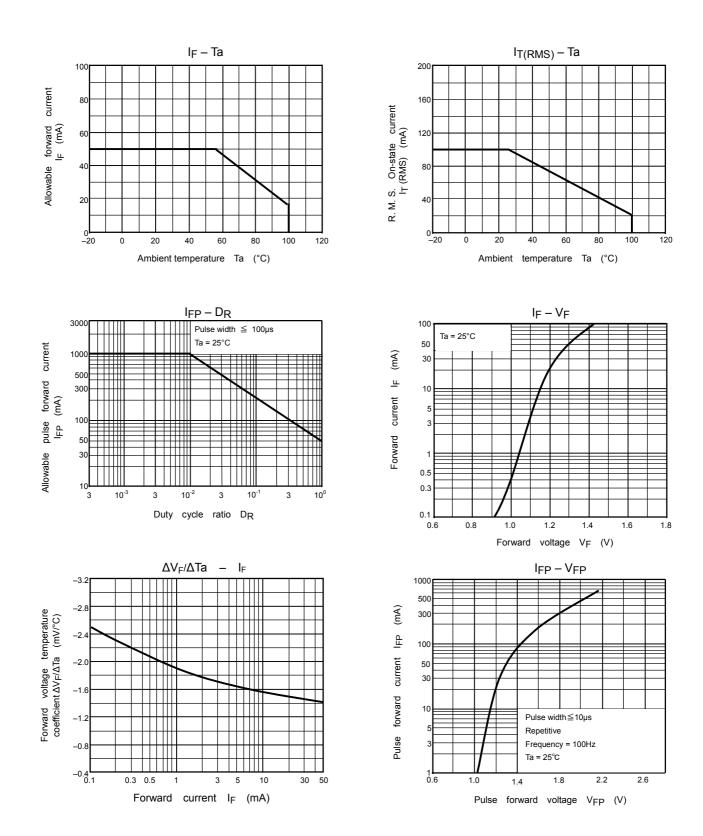
Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Trigger LED current	I _{FT}	$V_T = 3V, R_L = 100\Omega$	_	5	10	mA
Inhibit voltage	VIH	I _F = rated I _{FT}	-	_	40	V
Leakage in inhibited state	Ιн	I _F = rated I _{FT} V _T = rated V _{DRM}		100	300	μA
Capacitance (input to output)	CS	V _S = 0, f = 1MHz	_	0.8	_	pF
Isolation resistance	R _S	V _S = 500V	5×10 ¹⁰	10 ¹⁴	-	Ω
		AC, 1 minute	2500	_	_	V
Isolation voltage	BVS	AC, 1 second, in oil	_	5000	_	V _{rms}
		DC, 1 minute, in oil	_	5000	_	V _{dc}

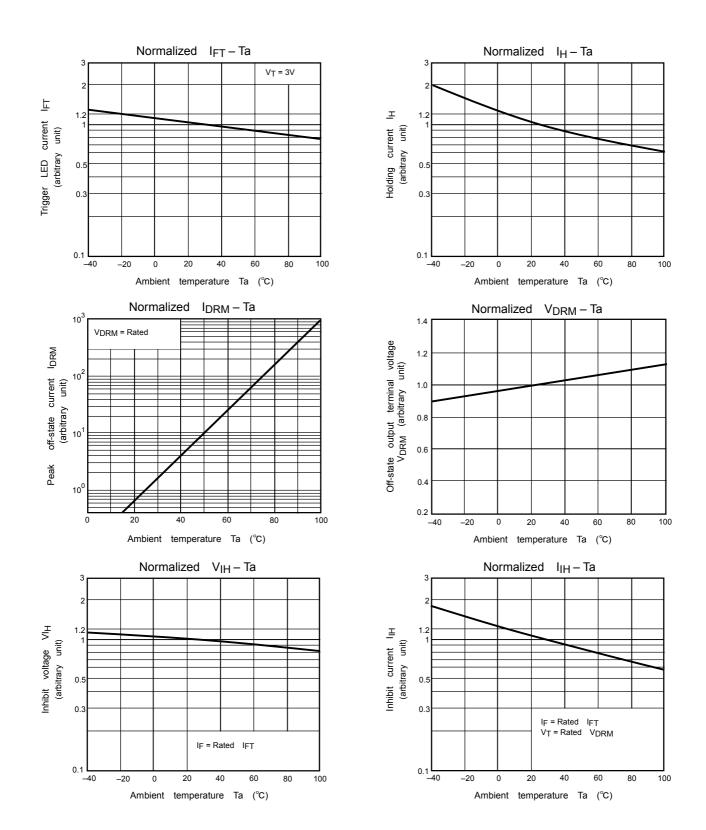
Fig.1: dv / dt test circuit



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